P-Channel Enhancement-Mode Vertical DMOS FETs

Ordering Information

BV_{DSS} / BV_{DGS}	$R_{DS(ON)}$ (max)	$V_{GS(th)}$ (max)	$I_{D(ON)}$ (min)	Order Number / Package		
				TO-92	TO-243AA*	Die†
-350V	25Ω	-2.4V	-0.4A	TP2535N3	—	—
-400V	25Ω	-2.4V	-0.4A	TP2540N3	TP2540N8	TP2540ND

* Same as SOT-89. Product supplied on 2000 piece carrier tape reels.
† MIL visual screening available.

Product marking for TO-243AA

TP5D✳

Where ✳ = 2-week alpha date code

Features

- ❏ Low threshold — -2.4V max.
- ❏ High input impedance
- ❏ Low input capacitance — 125pF max.
- ❏ Fast switching speeds
- ❏ Low on resistance
- ❏ Free from secondary breakdown
- ❏ Low input and output leakage
- ❏ Complementary N- and P-channel devices

Applications

- ❏ Logic level interfaces – ideal for TTL and CMOS
- ❏ Solid state relays
- ❏ Battery operated systems
- ❏ Photo voltaic drives
- ❏ Analog switches
- ❏ General purpose line drivers
- ❏ Telecom switches

Absolute Maximum Ratings

Drain-to-Source Voltage	BV_{DSS}
Drain-to-Gate Voltage	BV_{DGS}
Gate-to-Source Voltage	± 20V
Operating and Storage Temperature	-55°C to +150°C
Soldering Temperature*	300°C

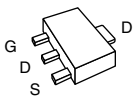
* Distance of 1.6 mm from case for 10 seconds.

Low Threshold DMOS Technology

These low threshold enhancement-mode (normally-off) transistors utilize a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces devices with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, these devices are free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Package Options



TO-243AA
(SOT-89)

TO-92

Note: See Package Outline section for dimensions.

11/12/01

Thermal Characteristics

Package	I_D (continuous)*	I_D (pulsed)	Power Dissipation @ T_A = 25°C	θ_{jc} °C/W	θ_{ja} °C/W	I_{DR}*	I_{DRM}
TO-92	-86mA	-0.6A	0.74W	125	170	-86mA	-0.6A
TO-243AA	-125mA	-1.2A	1.6W†	15	78†	-125mA	-1.2A

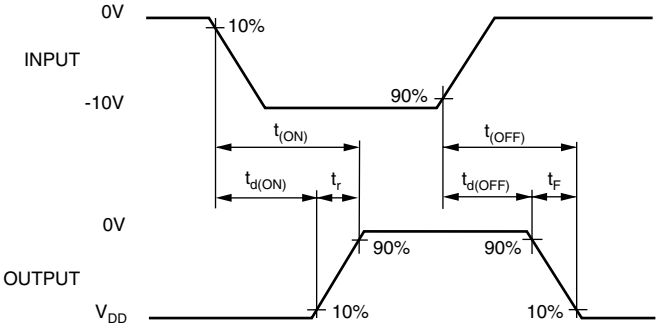
* I_D (continuous) is limited by max rated T_j.
† Mounted on FR5 Board, 25mm x 25mm x 1.57mm. Signficant P_D increase possible on ceramic substrate.

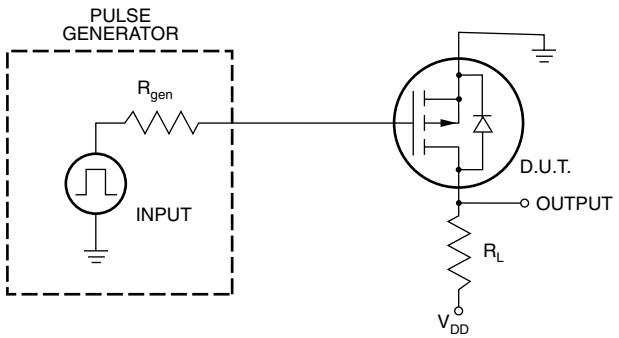
Electrical Characteristics (@ 25°C unless otherwise specified)

Symbol	Parameter		Min	Typ	Max	Unit	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	TP2540	-400			V	V_{GS} = 0V, I_D = -2mA
		TP2535	-350				
$V_{GS(th)}$	Gate Threshold Voltage		-1.0		-2.4	V	V_{GS} = V_{DS}, I_D = -1mA
$\Delta V_{GS(th)}$	Change in $V_{GS(th)}$ with Temperature				4.8	mV/°C	V_{GS} = V_{DS}, I_D = -1mA
I_{GSS}	Gate Body Leakage				-100	nA	V_{GS} = ±20V, V_{DS} = 0V
I_{DSS}	Zero Gate Voltage Drain Current				-10	µA	V_{GS} = 0V, V_{DS} = Max Rating
					-1.0	mA	V_{GS} = 0V, V_{DS} = 0.8 Max Rating T_A = 125°C
$I_{D(ON)}$	ON-State Drain Current		-0.2	-0.3		A	V_{GS} = -4.5V, V_{DS} = -25V
			-0.4	-1.1			V_{GS} = -10V, V_{DS} = -25V
$R_{DS(ON)}$	Static Drain-to-Source ON-State Resistance			20	30	Ω	V_{GS} = -4.5V, I_D = -100mA
				19	25		V_{GS} = -10V, I_D = -100mA
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with Temperature				0.75	%/°C	V_{GS} = -10V, I_D = -100mA
G_{FS}	Forward Transconductance		100	175		m℧	V_{DS} = -25V, I_D = -100mA
C_{ISS}	Input Capacitance			60	125	pF	V_{GS} = 0V, V_{DS} = -25V f = 1 MHz
C_{OSS}	Common Source Output Capacitance			20	70		
C_{RSS}	Reverse Transfer Capacitance			10	25		
$t_{d(ON)}$	Turn-ON Delay Time				10	ns	V_{DD} = -25V I_D = -0.4A R_{GEN} = 25Ω
t_r	Rise Time				10		
$t_{d(OFF)}$	Turn-OFF Delay Time				20		
t_f	Fall Time				13		
V_{SD}	Diode Forward Voltage Drop				-1.8	V	V_{GS} = 0V, I_{SD} = -100mA
t_{rr}	Reverse Recovery Time			300		ns	V_{GS} = 0V, I_{SD} = -100mA

Notes:
1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)
2. All A.C. parameters sample tested.

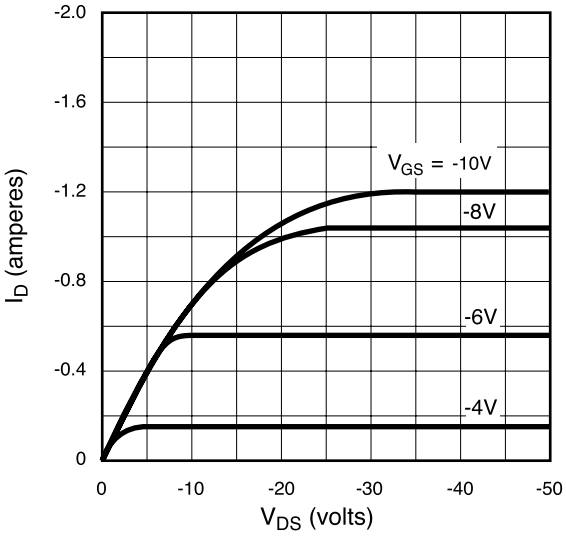
Switching Waveforms and Test Circuit



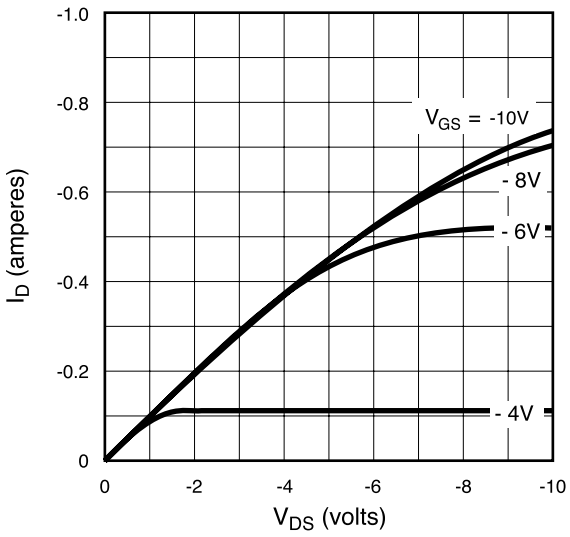


Typical Performance Curves

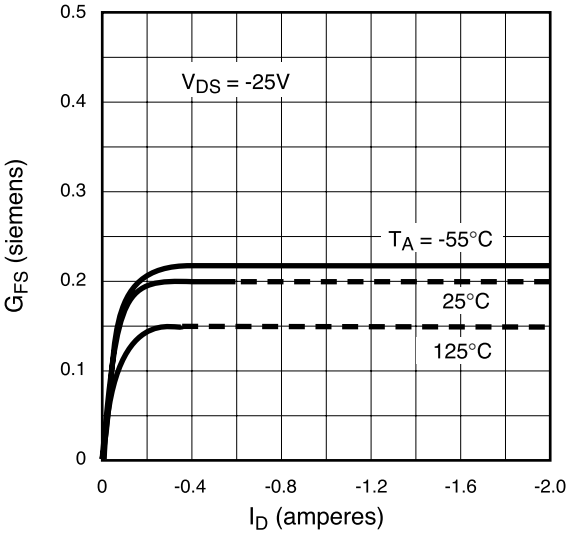
Output Characteristics



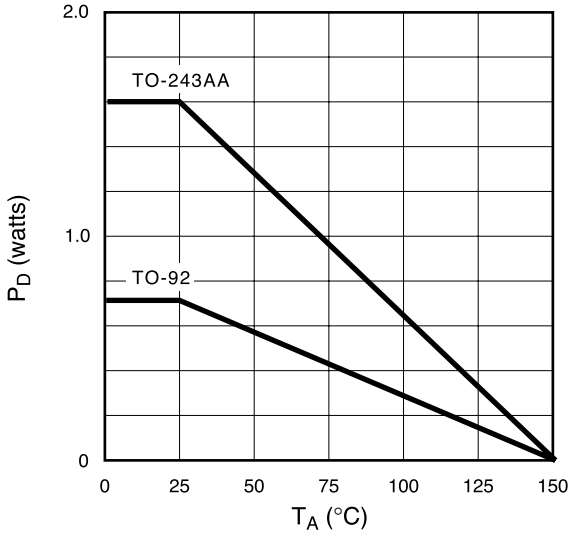
Saturation Characteristics



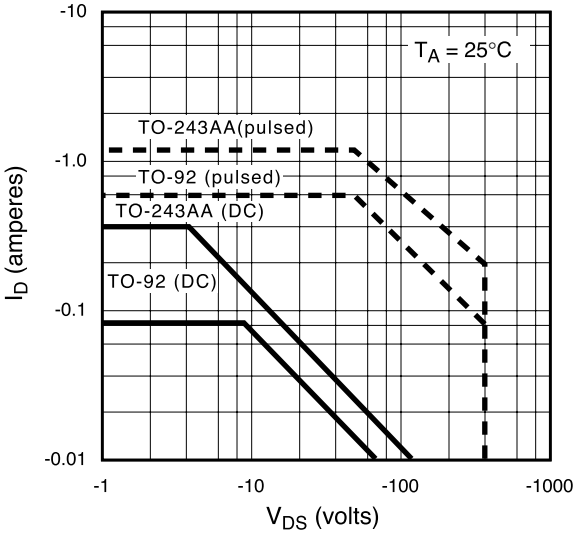
Transconductance vs. Drain Current



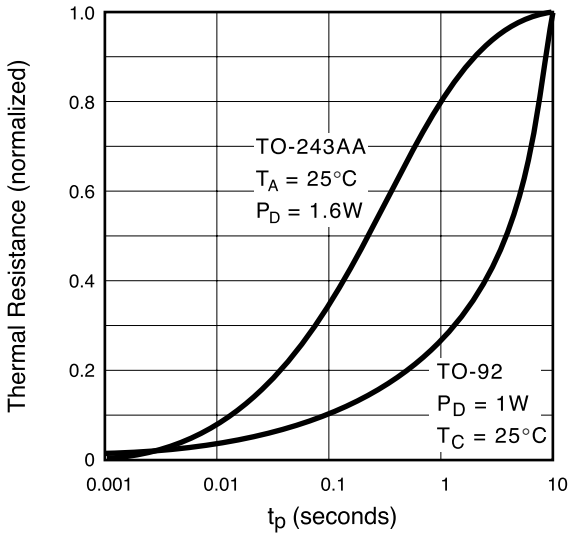
Power Dissipation vs. Ambient Temperature



Maximum Rated Safe Operating Area

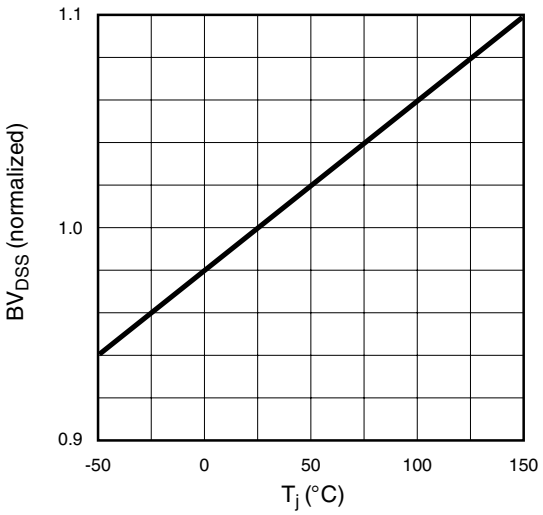


Thermal Response Characteristics

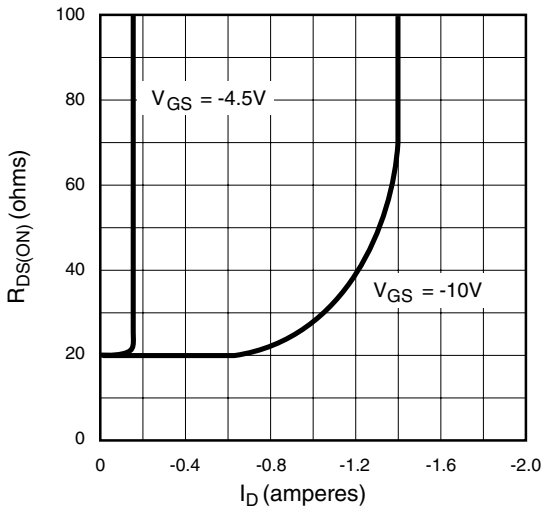


Typical Performance Curves

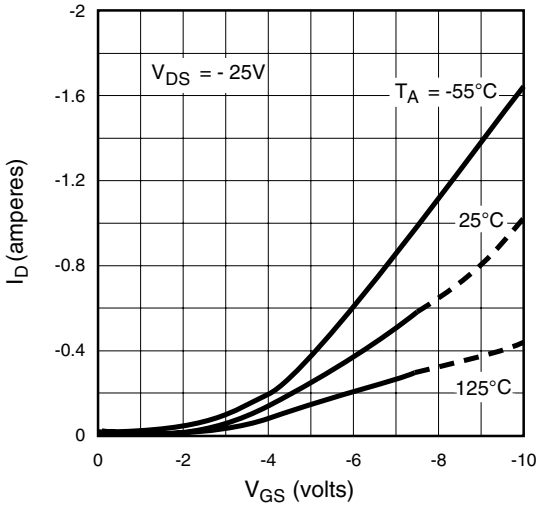
BV$_{DSS}$ Variation with Temperature



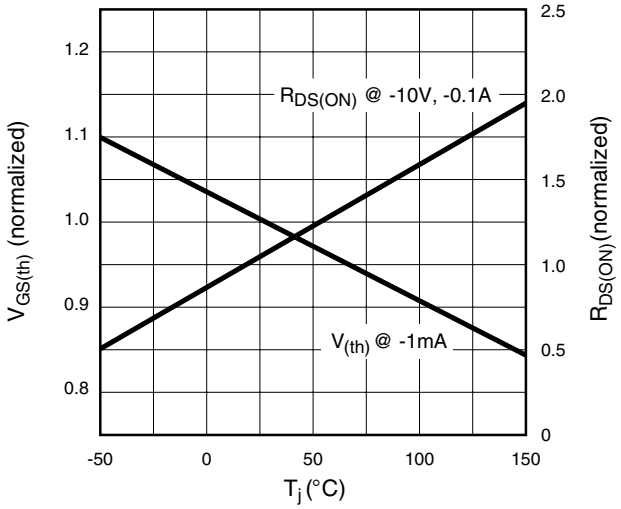
On-Resistance vs. Drain Current



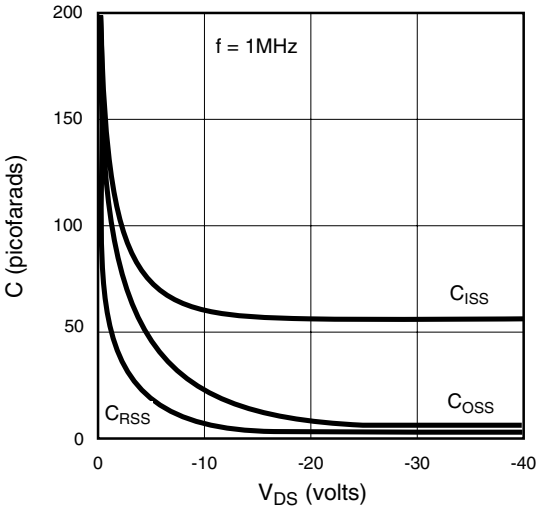
Transfer Characteristics



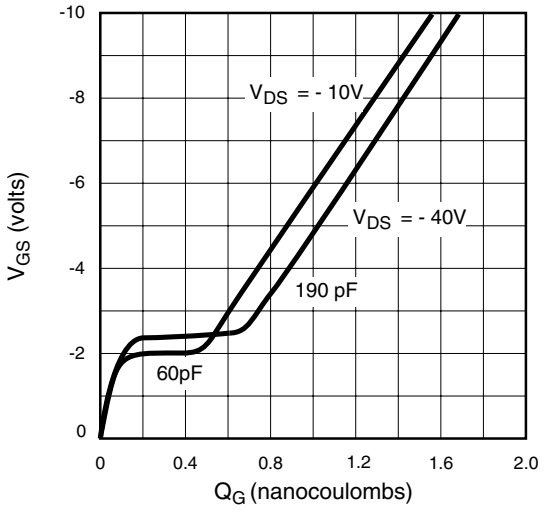
$V_{(th)}$ and R_{DS} Variation with Temperature



Capacitance vs. Drain-to-Source Voltage



Gate Drive Dynamic Characteristics



Supertex inc.

1235 Bordeaux Drive, Sunnyvale, CA 94089
TEL: (408) 744-0100 • FAX: (408) 222-4895
www.supertex.com